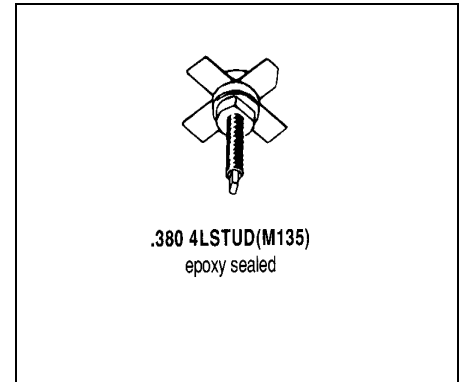


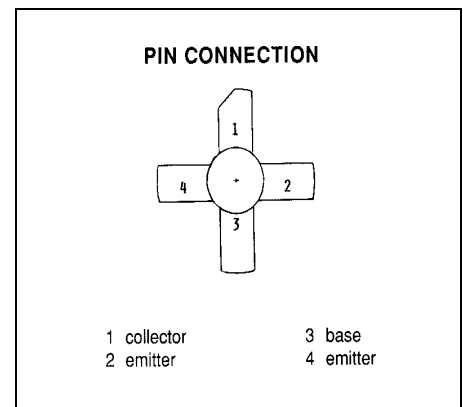
Features

- 150 MHz
- 28 VOLTS
- $P_{OUT} = 60W$
- $G_P = 7.0$ dB MINIMUM
- COMMON EMITTER CONFIGURATION



DESCRIPTION:

The MS1629 is an epitaxial silicon NPN transistor designed primarily for 12.5 V Class C, AM amplifier applications in the 118 - 136 MHz and 28 V Class C ground station transmitters. Emitter ballast resistors and gold metalization provide optimum VSWR capability.



ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	65.0	V
V _{CEO}	Collector-Emitter Voltage	35.0	V
V _{EBO}	Emitter-Base Voltage	4.0	V
P _{DISS}	Power Dissipation	75.0	W
I _C	Collector current	6.5	A
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)}	Thermal Resistance Junction-Case	2.3	°C/W
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Note : Above parameters , ratings , limits and conditions are subject to change .

ELECTRICAL SPECIFICATIONS (T_{case} = 25 °C)
STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{ces}	I _C = 200mA	V _{BE} = 0 m A	65.0	---	---	V
BV _{ceo}	I _C = 200 mA	I _B = 0 m A	35.0	---	---	V
BV _{ebo}	I _E = 10 mA	I _C = 0 m A	4.0	---	---	V
I _{cbo}	V _{CB} = 30 V	I _E = 10 m A	---	---	2.0	m A
H _{FE}	V _{CE} = 5.0V	I _C = 500 m A	10	---	150	---

DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 150 MHz	I _N P = 12W	V _{CE} = 28V	60.0	---	---	W
P _G	f = 150 MHz	I _N P = 12W	V _{CE} = 28V	7.0	---	---	dB
C _{OB}	V _{CB}	f = 1 MHz		---	---	80.0	pf

IMPEDANCE DATA

FREQ	Z _{IN} (Ω)	Z _{CL} (Ω)
150 MHz	1.0 + j2.0	4.0 - j3.9

Note : Above parameters , ratings , limits and conditions are subject to change.